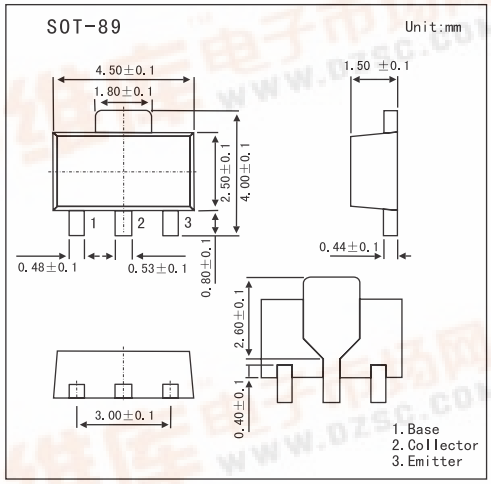
Silicon PNP Epitaxial Planar Type

2SB956



■ Features

- Large collector power dissipation PC
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Peak collector current	I_{CP}	-2	A
Collector power dissipation	P_C	1	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃ ±3℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = -1 mA, I_B = 0	-20			V
Emitter-base voltage	V_{EBO}	I_E = -10 μA, I_C = 0	-5			V
Collector-base cutoff current	I_{CBO}	V_{CB} = -10 V, I_E = 0			-1	nA
Forward current transfer ratio	h_{FE}	V_{CE} = -2 V, I_C = -500 mA	130		280	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -1 A, I_B = -50 mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = -500 mA, I_B = -50 mA			-1.2	V
Transition frequency	f_T	V_{CB} = -6 V, I_E = 50 mA, f = 200 MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB} = -6 V, I_E = 0, f = 1 MHz		40		pF

* Pulse measurement.

■ h_{FE} Classification

Marking	HR	HS
h_{FE}	130～210	180～280